

Amendments to and Listing of the Claims:

Please amend claims 5 and 9-11, and cancel claims 15-20, so that the claims read as follows:

1. (Original) A semiconductor cleaning method, comprising:

providing a semiconductor wafer;

forming a first layer of oxide over the semiconductor wafer;

forming a floating gate layer over the first layer of oxide;

forming a second layer of oxide over the floating gate layer;

etching the first layer of oxide, the floating gate layer, and the second layer of oxide to form a gate structure;

cleaning the semiconductor wafer including the gate structure using an ozonated de-ionized (DI) water;

further cleaning of the ozonated water-cleaned semiconductor wafer using a first cleaning solution; and

additional cleaning of the further cleaned semiconductor wafer using a second cleaning solution.

2. (Original) The method of claim 1, wherein the floating gate comprises polysilicon or nitride.

3. (Original) The method of claim 1, wherein the semiconductor wafer has formed therein at least one device.

4. (Original) The method of claim 1, wherein the semiconductor wafer has accumulated thereon contaminants accumulated during at least one previous processing step.

5. (Currently Amended) The method of claim 4, wherein the contaminants ~~comprises~~ comprise polymer.

6. (Original) The method of claim 5, wherein the polymer comprises photoresist.
7. (Original) The method of claim 1, wherein the first cleaning solution comprises a H₂O:H₂O₂:NH₄OH solution, wherein the proportions of H₂O:H₂O₂:NH₄OH are within the range of 1:1.5:4-80.
8. (Original) The method of claim 7, wherein the proportions of H₂O:H₂O₂:NH₄OH are 2.1:3.1:80.
9. (Currently Amended - Withdrawn) The method of claim 1, wherein the first cleaning solution comprises a H₂O:H₂O₂:HCl H₂O:H₂O₂:HCl solution, wherein the proportions of H₂O:H₂O₂:HCl H₂O:H₂O₂:HCl are within the range of 1:1.5:4-80.
10. (Currently Amended - Withdrawn) The method of claim 9, wherein the proportions of H₂O:H₂O₂:HCl H₂O:H₂O₂:HCl are 1.3:2.2:80.
11. (Currently Amended - Withdrawn) The method of claim 1, wherein the first cleaning solution comprises a HF:HCl:H₂O HF:HCl:H₂O solution, wherein the proportions of HF:HCl:H₂O HF:HCl:H₂O are 1:1.3.400.
12. (Original) The method of claim 1, wherein the concentration of ozone in the ozonated DI water is within the range of 10-80 ppm.
13. (Original) The method of claim 12, wherein the concentration of ozone in the ozonated DI water is 40 ppm.
14. (Original) The method of claim 1, wherein the second cleaning solution comprises an ozonated DI water.
- 15-20. (Canceled)